

## AMENDMENTS TO THE SPECIFICATION

Page 9, amend the paragraph beginning on line 13 to read as follows.

Particularly the present invention is effective in the case where the first interlayer insulation layer is an anodic oxide film, and the second interlayer insulation layer is formed by a deposition process which forms a non-anode insulation film. In addition, the present invention is effective in the case where the lower electrode is made of Al or an Al alloy, the first interlayer insulation layer is an anodic oxide film of the Al or Al alloy of the lower electrode, and the second interlayer insulation layer is made of an insulation film material, which is a non-anodic insulation film material, and which can be selectively etched with respect to the lower electrode and the anodic oxide film thereof.

Page 21, amend the paragraph beginning on line 7 as follows.

Particularly as the material of the second interlayer insulation layer 15, an insulation film material which can be selectively etched with respect to Al or an anodic oxide film thereof is desired. For example, an insulation film material<sub>1</sub> such as Si oxide, which is a non-anodic insulation film material, or Si nitride<sub>1</sub> which is a non-anodic nitride film material, that can be dry-etched with CF<sub>4</sub> is preferred. In a dry etching method using fluoride-based etching gas such as CF<sub>4</sub> or the like, Si oxide or Si nitride can be etched at a high selection ratio with respect to Al or an Al alloy of the lower electrode and the anodic oxide film thereof.